

BRIEF DESCRIPTION OF THE DRAWINGS

The present invention will become better understood with reference to the accompanying drawings which are given
5 only by way of illustration and thus are not limitative of the present invention, wherein:

Fig. 1 is a SEM photograph showing oxidation of a TiN layer without a bonding layer in accordance with the conventional method for manufacturing capacitor of
10 semiconductor device.

Fig. 2 is a SEM photograph showing oxidation of a portion of a TiN layer adjacent to a bonding layer in accordance with a conventional method for manufacturing capacitor of semiconductor device.

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08/02/05 15 Figs. 3a ^{through} and 3d are cross-sectional diagrams illustrating a method for manufacturing capacitor of semiconductor device in accordance with the present invention.

Fig. 4 a SEM photograph showing a TiN layer adjacent
20 to a bonding layer without any oxidation thereof in accordance with the method for manufacturing capacitor of semiconductor device of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS